PVMOS manual

B.E. Pieters*

Institut für Energie und Klimaforschung - IEK5 Photovoltaik,
Forschungszentrum Jülich, 52425 Jülich, Germany
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I. INTRODUCTION

This is (or rather will be as the current state of this document is far from finished) the manual for the Photo-Voltaic MOdule Simulator (PVMOS). PVMOS is an ordinary differential equation solver using finite-differences specifically designed to electrically model solar modules. For more information on how that works I refer the reader to [1]. The purpose of this document is to document how PVMOS is operated and installed. In the following sections I discuss in order, the installation, basic usage and operating principles and finally a detailed discussion of all available functions.

II. DISCLAIMER

If this software ever does anything you think I claim it does or should do, consider yourself lucky.

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This program comes with ABSOLUTELY NO WARRANTY. This is free software, and you are welcome to redistribute under certain conditions. You should have received a copy of the GNU General Public License along with this program. If not, see http://www.gnu.org/licenses/.

III. BASIC USAGE AND OPERATING PRINCIPLES

The input for PVMOS is a plain text file with commands. To solve a problem PVMOS is typically called from the command line with as an argument the file name describing the problem. With these input files you can specify the geometry of your solar cell/module including the local properties such as electrode sheet resistances and solar cell properties. You can also specify which calculations you want PVMOS should perform and what data to save. A call to PVMOS from the command line looks like this

pvmos [verbose-option] <input-file>

where [verbose-option] is an option which how much information PVMOS outputs to stdout, and <input-file> is the plain text input file. We first describe the mesh data structure in more detail.

In its essence PVMOS is a Poisson solver. The Poisson equation is solved for several stacked, 2D "electrodes", where each electrode is coupled to the electrodes above and below (note that a stack of 2D electrodes makes a 3D structure). The electrodes itself are simply conductors and behave linearly (Ohmic). However, the connection between the electrodes can be non-linear (e.g. a diode). Now, there are several limitations of the structures that PVMOS handles. The main limitation is that the meshes are 2D as in PVMOS all electrodes share the same 2D mesh. This means that PVMOS is specifically designed for flat layered structures. PVMOS uses straight forward finite-differences to solve the coupled Poisson equations. As such the 2D meshes in PVMOS divide the 2D surface in rectangular elements. Now every element in the mesh must be associated with certain properties. Storing properties on a per element basis would put a heavy burden on the memory resources. For that reason elements are grouped into "areas" where each area constitutes a certain combination of properties. A mesh therefore also contains a list of all areas and every element is a member of one of the areas in the mesh (note that an element is always assigned

^{*}Electronic address: b.pieters@fz-juelich.de

to one area, i.e. you need at least one area for every unique combination of local properties). Also note that as all electrodes share the same 2D mesh, one area contains the properties for all electrodes and connections between them.

The PVMOS input file is processed sequentially and contains commands that create or modify meshes, perform a simulation, or export data to a file. A complete list of commands is presented in Section VIA. In PVMOS we can define more than one mesh at the same time. This is useful as it allows you to create new meshes by joining two meshes, e.g., to create several series connected cells in a thin-film module. In order to reference one particular mesh, each mesh has a name. This name must thus be provided to any command that operates on a mesh. Likewise, some commands operate on an area within a mesh and thus areas also have a name. To reference an area within a mesh we use the following syntax <mesh-name>.<area-name>, i.e. the name of the mesh followed by a dot and the name of the area within that particular mesh. Sometimes we need to select elements in a mesh (for example when we want to assign a set of elements to a certain area). To this end each mesh has a list of selected elements. If you select elements in a mesh the list is occupied by the element ID's, after which you can do operations on the selected elements. Note that elements are selected on a per mesh basis.

It may be useful to store intermediate results, especially as sometimes creating the mesh may take some time and you want to do many different calculations based on the same mesh. For such cases PVMOS has a binary file format to store complete meshes with all elements, areas, properties and simulation results. This mesh may be loaded later to continue where you left of. The primary focus is to store intermediate results and as such not much value is put on compatibility between different PVMOS versions, i.e. compatibility between the file format of different PVMOS versions is not guaranteed (in general compatibility will break if a new version makes any change in the mesh data structures). The binary format is also used for a dynamic library for GNU Octave (an open source tool largely compatible with Matlab), which allows you to generate a mesh for PVMOS within octave and store it in binary form for use in PVMOS.

IV. INSTALLATION INSTRUCTIONS

PVMOS is a command-line application written entirely in C. For the operation PVMOS depends on several libraries, most notably cholmod, for the solving of sparse linear systems. PVMOS has been tested on Linux and Windows systems. To install PVMOS you need to either compile the source, for which a Makefile is provided, or you need to download pre-compiled binaries for your system (if available).

A. Compiling from source

Here are the instructions to compile the PVMOS executable:

- 1. Install PVMOS's dependencies (BLAS and CHOLMOD). These libraries should be readily available in most linux distributions. Take care to install the development files (i.e. headers) for these libraries too
- 2. Edit the Makefile, in particular you may have to change the BLAS library to link to (the used BLAS library has a relatively large impact on performance, see below) or change the install directory
- 3. type "make", and "make install"

The performance of PVMOS is typically strongly dependent on the performance of the sparse linear solver (i.e. cholmod). For an optimal performance an optimized BLAS library must be used (the reference BLAS is comparatively slow). For an optimized BLAS there are several options. One option is to use ATLAS which is available for all common CPU architectures and gives a decent performance. On some architectures you can use OpenBLAS (OpenBLAS is an actively developed fork of the now unmaintained GoTo BLAS), which generally performs better than ATLAS. Some CPU manufacturers also publish their own optimized BLAS libraries for their CPU's (e.g. Intel and AMD). Per default the make-files are set up to use OpenBLAS as it provides a good performance on the most common desktop CPU architectures and is freely available.

B. Pre-compiled binaries (Windows)

There are two pre-compiled versions for windows, 32 and 64 bit. If your system supports it I suggest to use 64 bit as 32 bit applications are rather limited in the maximum allocatable memory space (¡ 2Gb), you may run into this limit for larger problems. The binary distribution consists of an executable with several dll's. The installation procedure

for PVMOS manual as no installer is provided (you can help PVMOS by making one). So here is the procedure for a binary install:

- 1. Download the binary
- 2. Unpack the files in a directory of your choise
- 3. Optional: Add the path to your PVMOS executable to the PATH variable

1. Setting the "PATH" variable

A properly set PATH variable will allow you to execute PVMOS from the command line without typing the full path to the PVMOS executable. Here I describe how to edit your path variable in Windows 7. First another word of warning. Adding things to the path variable is mostly harmless, however, if you break your path string (e.g. delete a part) you may seriously impair the functioning of programs that need the path variable. Follow these instructions on your own risk!

- 1. Click on the start menu
- 2. type "PATH" in the "search programs and files" field, you should now find options to edit the path variable for the system of for the current user, select to edit it for the current user
- 3. Select the path variable
- 4. Click on Edit
- 5. Scroll to the end of the string and add; <installation directory>, where <installation directory> points to the location of your PVMOS executable
- 6. Click on OK
- 7. Click on OK

C. Installing the GNU-Octave PVMOS-mesh package

The PVMOS package for GNU Octave is a set of tools to create and save binary PVMOS meshes from within GNU Octave. A more detailed description of the package can be found in Section VII. Installing the PVMOS package in Octave is through the "pkg" command, i.e. the usual procedure to install packages in GNU Octave. Prepared packages are available for download and are named PVMOS-mesh-¡version¿.tar.gz. The package can also be created from source using "make PVMOS-mesh.pkg". After installing the package you can use "pkg load PVMOS-mesh" to load the functions for use.

V. RECOMMENDED SOFTWARE

Obviously you are free to use whatever software you want. However, to process data from PVMOS or to get data into PVMOS I often use file formats which will not be supported by all software packages. I thus here detail my software setup in the hope it helps you. All software here is free and open source software.

A. Get data into PVMOS: GNU Octave & Inkscape

These programs are useful when defining complex geometries. If you want to define complex geometries in PVMOS there are basically three ways:

1. Use the PVMOS scripting language. The advantages of this method is that it can be very accurate and fast and is independent of any other software, the downside is that it quickly becomes tedious

- 2. mkpvmosmesh with GNU Octave. This allows you to use all the data and image processing power of Octave to generate meshes. However, this library only allows you to create mesh topologies consisting of rows and columns (i.e. meshes easily defined with a matrix
- 3. Define geometries using polygons. PVMOS has good support for polygons to select and specify various areas in your device. Complicated shapes may be created in a graphics program such as inkscape and exported to PVMOS. For this I have an extension to export data from inkscape for use in PVMOS. In combination with the trace bitmap feature of inkscape you can quickly define appropriate polygons for complicated geometries if you provide a bitmap image, e.g. you can create a polygon for the metalization pattern of a device by tracing a picture. This method potentially has a lower memory footprint compared to the GNU Octave option.

Inkscape is a powerful vector graphics tool. One of the graphics objects Inkscape supports are "paths". In its simplest form a path is simply a polygon. As PVMOS can use polygons when defining a mesh it makes sense to use a tool such as Inkscape to create the polygons as Inkscape provides a powerful, graphical, means to do so. In order to get the polygon data out of inkscape I created a simple extension which extracts the data out of a polygon. To use this extension select a path with polygon data and select the ExportXY extension, a popup window will come up with coordinates you can select and paste in a polygon data file. Note however that Inkscape paths may also be bezier curves, which PVMOS does not support. To use the extension is is thus required that the path data is forced to be a polygon. For this you can use the flatten Bezier extension in Inkscape. I have not fully dug into Inkscape's internal units. This can be tricky as Inkscape may use all sorts of transforms on objects. This means that the polygon data may need to be scaled, rotated, mirrored and shifted to get the data in the correct unit. For this I provide a small CLI program "transformpolygon".

B. Analyse simulated data: Gnuplot

The data-format that PVMOS uses for element-wise data export is laid out such that Gnuplot can make sense out of the data. Other plotting tools may not support this format. The element-wise data export allows you to export data from the mesh on a per-element basis and is particularly useful for inspecting meshes to ensure a correct mesh definition. For this reason I recommend the use of Gnuplot. Other data formats that PVMOS should not be a problem for other plotting tools.

VI. PVMOS INPUT FILE FORMAT

A. Command Reference

Creating Meshes	
Keyword	Description
newmesh	Create a new, rectangular mesh. The command takes seven arguments:
	1. x1, x-coordinate of the lower left corner
	2. y1, y-coordinate of the lower left corner
	3. x2, x-coordinate of the upper right corner
	4. y2, y-coordinate of the upper right corner
	5. Nx, Number of elements in x direction
	6. Ny, Number of elements in y direction
	7. mesh-name, Name of the new mesh

joinmesh

Create new mesh by joining two meshes. Make sure the meshes touch but do not overlap. The function takes offset values as input which allow you to "shift" the second mesh to align it to the first. The command takes 5 arguments:

- 1. x_off, x-offset in coordinate system of the second mesh
- 2. y_off, y-offset in coordinate system of the second mesh
- 3. mesh1-name, Name of the first mesh
- 4. mesh2-name, Name of the second mesh
- 5. mesh3-name, Name of the resulting mesh

joinmesh_h

Create new mesh by joining two meshes. Make sure the meshes touch but do not overlap. The function takes a y-offset value as input which allow you to "shift" the second mesh in the y-direction to align it to the first. The x-offset value is the maximal x-value found in the first mesh. The command takes 4 arguments:

- 1. y_off, y-offset in coordinate system of the second mesh
- 2. mesh1-name, Name of the first mesh
- 3. mesh2-name, Name of the second mesh
- 4. mesh3-name, Name of the resulting mesh

joinmesh_v

Create new mesh by joining two meshes. Make sure the meshes touch but do not overlap. The function takes an x-offset value as input which allow you to "shift" the second mesh in the x-direction to align it to the first. The y-offset value is the maximal y-value found in the first mesh. The command takes 4 arguments:

- 1. x_off, x-offset in coordinate system of the second mesh
- 2. mesh1-name, Name of the first mesh
- 3. mesh2-name, Name of the second mesh
- 4. mesh3-name, Name of the resulting mesh

dupmesh

Duplicate a mesh. The command takes 2 arguments:

- 1. mesh1-name, Name of the mesh to be duplicated
- 2. mesh2-name, Name of the resulting copy

add_electrode

Adds an electrode to a certain mesh. The command takes one argument:

1. mesh-name, Name of the mesh

Transforming Meshes

Description

move

Move a mesh in x- and y-directions. The command takes three arguments:

- 1. mesh-name, Name of the mesh
- 2. delta x, move distance in x-direction
- 3. delta y, move distance in y-direction

rotate

Rotate mesh around a center coordinate. Rotation can only be performed over multiples of 90 degrees. The command takes four arguments:

- 1. mesh-name, Name of the mesh
- 2. x, x-coordinate of rotation center
- 3. y,y-coordinate of rotation center
- 4. d, degrees to rotate over (must be a multiple of 90)

flipx

Mirror a mesh in the y-axis. The command takes one argument:

1. mesh-name, Name of the mesh

flipy

Mirror a mesh in the x-axis. The command takes one argument:

1. mesh-name. Name of the mesh

scale

Scale all coordinates in a mesh. The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. f, scaling factor

scalex

Scale all x-coordinates in a mesh. The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. f, scaling factor

scaley

Scale all y-coordinates in a mesh. The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. f, scaling factor

boundingbox

Change the mesh bounding box. This argument scales and moves a mesh such that it fits in a specified rectangle (the bounding box). The mesh is either scaled preserving the aspect ratio or without preserving it. The command takes six arguments:

- 1. mesh-name, Name of the mesh
- 2. x1, x-coordinate of the lower left corner of the bounding box
- 3. y1, y-coordinate of the lower left corner of the bounding box
- 4. x2, x-coordinate of the upper right corner of the bounding box
- 5. y2, y-coordinate of the upper right corner of the bounding box
- 6. R, Argument can be either 0, do not preserve mesh aspect ratio, or 1, preserve mesh aspect ratio.

SELECTING ELEMENTS

Keyword select_rect

Description

Select a rectangular area in a mesh. If currently nodes are already selected in the mesh, the command selects the subset of selected nodes within the rectangle. If the latter is not desired use deselect first. The command takes five arguments:

- 1. x1, x-coordinate of the lower left corner of the selected rectangle
- 2. y1, y-coordinate of the lower left corner of the selected rectangle
- 3. x2, x-coordinate of the upper right corner of the selected rectangle
- 4. y2, y-coordinate of the upper right corner of the selected rectangle
- 5. mesh-name, Name of the mesh

select_rect_contour

Select the contour of a rectangle in a mesh. If currently nodes are already selected in the mesh, the command selects the subset of selected nodes within the rectangle. If the latter is not desired use deselect first. The command takes six arguments:

- 1. x1, x-coordinate of the lower left corner of the selected rectangle
- 2. y1, y-coordinate of the lower left corner of the selected rectangle
- 3. x2, x-coordinate of the upper right corner of the selected rectangle
- 4. y2, y-coordinate of the upper right corner of the selected rectangle
- 5. d, distance from the contour within which elements are selected
- 6. mesh-name, Name of the mesh

select_circ

Select a circular area in a mesh. If currently nodes are already selected in the mesh, the command selects the subset of selected nodes within the circle. If the latter is not desired use deselect first. The command takes four arguments:

- 1. x_c, center x-coordinate of the selected circle
- 2. y_c, center y-coordinate of the selected circle
- 3. r, radius of the selected circle
- 4. mesh-name, Name of the mesh

select_circ_contour

Select the contour of a circle in a mesh. If currently nodes are already selected in the mesh, the command selects the subset of selected nodes within the circle. If the latter is not desired use deselect first. The command takes five arguments:

- 1. x_c, center x-coordinate of the selected circle
- 2. y_c, center y-coordinate of the selected circle
- 3. r, radius of the selected circle
- 4. d, distance from the contour within which elements are selected
- 5. mesh-name, Name of the mesh

select_poly

Select an area within a polygon-contour. In order to use this command you must first load or define a polygon from file with the load_poly or define_poly commands. If currently elements are already selected in the mesh, the command selects the subset of selected elements within the polygon. If the latter is not desired use deselect first. If a polygon circles an element more than once the node is selected if the node is circled an uneven number of times. This allows one to define polygon areas with holes. To make a hole, define one outer part of the polygon and one inner part and have a break between these tho parts, i.e. the two parts should not be connected by a line segment, (see load_poly and loaddefine_poly). The command takes one argument.

1. mesh-name, Name of the mesh

select_poly_contour

Select an area around a polygon-contour. In order to use this command you must first load or define a polygon from file with the load_poly or define_poly commands. If currently elements are already selected in the mesh, the command selects the subset of selected elements near to the polygon. If the latter is not desired use deselect first. This command is often useful to refine the mesh along the polygon before using select_poly to assign elements to a new area. It may also be useful to define things such as cracks. If no line segment is present between two seubsequent coordinates in the polygon (i.e. a break in the polygon), no nodes are selected between these coordinates. The command takes three arguments.

- 1. $\mbox{distance},$ Distance from the polygon
- 2. loop, Argument takes either 0 (not looped) or 1 (looped). In looped modus the last point in the polygon is connected to the first point.
- 3. mesh-name, Name of the mesh

load_poly

Load a polygon from file. This command is used in conjunction with the select_poly and the select_poly_contour commands. Once a polygon is loaded you can use it to select until a new load_poly command is given. Polygons may contain breaks (i.e. absence of a line segment between two coordinates). The command takes one argument.

1. file-name, Name of the file describing the polygon (one 2D coordinate per line, i.e., two columns, 1: x-coordinate, 2: y-coordinate, empty lines indicate a break)

define_poly

Define polygon within the input file. See also the load_poly command for an alternative method. The difference between this command and the load_poly command is that with this command you can define the polygon within the PVMOS input file. As such it is best suited for simple polygons. The define_poly command marks the start and the end of a table defining the polygon. Between the two define_poly commands, one coordinate (x- and y-value) per line is expected and an empty line indicates a break, i.e.,

define_poly

x_1	y_1
x_2	y_2
x_3	y_3
•••	•••
x_N	y_N
x_{N+1}	y_{N+1}

define_poly

 x_M

where (x_i, y_i) is the *i*-th coordinate of the polygon and between coordinates N and N+1 there is a break.

select_area

Select all nodes assigned to a given area. If currently nodes are already selected in the mesh, the command selects the subset of selected nodes which are assigned to the given area. If the latter is not desired use deselect first. The command takes one argument.

1. area-name, Name of the mesh and area (<mesh-name>.<area-name>)

deselect

deselects a selection within a mesh. The command takes one argument.

1. mesh-name, Name of the mesh

Manually changing the mesh topology

Keyword

Description

split_x

Split selected elements in x-direction. If no elements are selected, all elements are split. As the topology of the mesh changed all selected nodes in the mesh are un-selected after this command. The command takes one argument

1. mesh-name, Name of the mesh

split_y

Split selected elements in y-direction. If no elements are selected, all elements are split. As the topology of the mesh changed all selected nodes in the mesh are un-selected after this command. The command takes one argument

1. mesh-name, Name of the mesh

split_xy

Split selected elements in both x- and y-direction. If no elements are selected, all elements are split. As the topology of the mesh changed all selected nodes in the mesh are un-selected after this command. The command takes one argument

1. mesh-name, Name of the mesh

split_long

Split selected elements in their longest direction. If no elements are selected, all elements are split. As the topology of the mesh changed all selected nodes in the mesh are un-selected after this command. The command takes one argument

1. mesh-name, Name of the mesh

split_coarse

Split selected elements until the node-edges are all smaller than a given length. If no elements are selected, all elements are split. As the topology of the mesh changed all selected nodes in the mesh are un-selected after this command. The command takes three arguments

- 1. mesh-name, Name of the mesh
- 2. lx, Maximum edge length in x-direction
- 3. ly, Maximum edge length in y-direction

resolve_rect

Split elements along the edges of a rectangle until all element edges are smaller than a given length. This command can be used to ensure a particular rectangle fits accurately in the mesh. The command takes six arguments

- 1. mesh-name, Name of the mesh
- 2. 1, Maximum edge length
- 3. x1, x-coordinate of the lower left corner of the selected rectangle
- 4. y1, y-coordinate of the lower left corner of the selected rectangle
- 5. x2, x-coordinate of the upper right corner of the selected rectangle
- 6. y2, y-coordinate of the upper right corner of the selected rectangle

resolve_circ

Split elements along the circumference of a circle until all element edges are smaller than a given length. This command can be used to ensure a particular circle fits accurately in the mesh. The command takes five arguments

- 1. mesh-name, Name of the mesh
- 2. 1, Maximum edge length
- 3. x_c, center x-coordinate of the selected circle
- 4. y_c, center y-coordinate of the selected circle
- 5. r, radius of the selected circle

resolve_poly

Split elements along the contour of a polygon until all element edges are smaller than a given length. This command can be used to ensure a particular polygon fits accurately in the mesh. The command requires a polygon to be defined with either define-poly or load-poly. Breaks in the polygon are not resolved, i.e. the routine only resolves the line segments within the polygon. The command takes three arguments

- 1. mesh-name, Name of the mesh
- 2. 1, Maximum edge length
- 3. c, Loop the polygon or not (1, loop, i.e. resolve the line segment between the start and end coordinates, 0 do not loop)

simplify

Attempt to simplify a mesh. If elements are selected they are un-selected as the topology of the mesh changed. The command takes one argument

1. mesh-name, Name of the mesh

SAVING AND LOADING MESHES

Keyword

Description

savemesh

Save a mesh to file in the PVMOS binary format, so it can be loaded again at a later time (see the loadmesh command). Compatibility of the saved meshes with past or future versions of PVMOS is not guaranteed. The command takes two arguments.

- 1. mesh-name, Name of the mesh to be saved.
- 2. file-name, file name to save the mesh to.

loadmesh

Load a mesh saved to file in the PVMOS binary format (see the savemesh command). The command takes two arguments.

- 1. file-name, file name of the file containing the mesh data.
- 2. mesh-name, Name to assign to the loaded mesh

Element-wise export of data

Keyword

Description

printmesh

Export the mesh in a manner that is compatible with (probably only) Gnuplot (www.gnuplot.info/). The resulting plot draws the contour of each element in the mesh. If a selection of elements is made for the mesh, only the selected nodes are plotted. The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, file-name to save the data in.

The output file will contain coordinates in columns. For each element the file contains the coordinates of the lower left- and the upper right corners empty line:

x1 y1 x2 y1 x2 y2 x1 y2 <empty line>

printconn

Print lateral connections in the electrodes in a format compatible with Gnuplot (www.gnuplot.info/). When plotting the file (with vectors) a vector is drawn between the center of each element to the center of the adjacent elements to which it is connected. If a selection of elements is made for the mesh, only the selected nodes are plotted. This routine may be useful when inspecting generated meshes. The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, filename to save the data in.

The output is coordinates in columns. For each element the file contains the following data where xc, yc is the center of the current element and xca_i, yca_i is the center coordinate of the i-th adjacent

```
xc yc xca_1 yca_1 element: xc yc xca_2 yca_2
```

printarea

Print the geometry of the mesh which identifies each element and the area it belongs to. The file-format is laid out such that it is compatible with a surface plot in Gnuplot (www.gnuplot.info/). If a selection of elements is made for the mesh, only the selected nodes are plotted. The command takes two arguments:

- 1. mesh-name. Name of the mesh
- 2. file-name, file-name to save the data in.

The output file will contain data in columns. The file contains coordinates, the element ID and the corresponding area ID. Note that the parameters for each area can be exported with the printpars command. For each element it plots 2 times 2 data lines with an empty line in-between. Between the data of two elements are two empty lines. This file is formatted such that when plotted with "splot" in gnuplot you can plot a surface for each element in the mesh, which allows you to see the areas in the defined geometry. For each element the following data is printed to the file:

printV

Print the electrode potentials per element for each stored solution. The output is formatted for gnuplot's splot command, such that a surface plot plots each element individually. If a selection of elements is made for the mesh, only the selected nodes are plotted. The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, file-name to save the data in.

The output file will contain data in columns. The file contains coordinates followed by the potential in each electrode for each solution. For each element it plots 2 times 2 data lines with an empty line in-between. Between the data of two elements are two empty lines. This file is formatted such that when plotted with "splot" in gnuplot you can plot a surface for each electrode in each element in the mesh. For each element the following data is printed to the file, where the subscripts indicate the electrode index and the superscript the solution index:

```
electrode index and the superscript the solution index:  
x1    y1    V_0^1 \ V_1^1 \ V_{...}^1 \ V_N^1 \ V_0^2 \ V_1^2 \ V_{...}^2 \ V_N^2 \ ...  
x1    y2    V_0^1 \ V_1^1 \ V_{...}^1 \ V_N^1 \ V_0^2 \ V_1^2 \ V_{...}^2 \ V_N^2 \ ...  
<a href="#">
<empty line></a>
<a href="#">
<a hr
```

printpar

Print a summary of the parameters per area, including both area-name and area-ID. The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, file-name to save the data in.

print_solpar

Export the solar cell parameters. Exports a file with I_{sc} , V_{oc} , I_{mpp} , V_{mpp} , FF and P_{max} . The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, file-name to save the data in.

printIV

Export the IV characteristics of the device. Exports a file with two columns, the first contains the applied voltage and the second the corresponding simulated total current. The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, file-name to save the data in.

printInIp

Integrate external currents over selected elements. Exports a file with four columns, the applied voltage, the integrated current injected from the positive node, the integrated current emitted to the negative node, and the total current over the whole device. This may be used for sanity checking of the solution or, if your device has more than one connection to the applied bias, to distinguish between the connections (e.g. extract the current injected through one particular bus-bar). The command takes two arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, file-name to save the data in.

printlocalJV

Print a JV characteristics for one particular location and one inter-electrode index. This is useful to check the PVMOS diode model. That command takes 8 parameters:

- 1. mesh-name, Name of the mesh
- 2. x, x-coordinate
- 3. y, y-coordinate
- 4. i, inter-electrode index
- 5. Vstart, Start voltage for the JV characteristics
- 6. Vend, End voltage for the JV characteristics
- 7. Nstep, Number of voltage steps in the JV characteristics
- 8. file-name, file-name to save the data in.

surfVplot

Export the electrode voltages for a specific solution. Unlike the print-commands like printV the data is interpolated and mapped on a regular mesh. The command takes eight arguments:

- 1. mesh-name, Name of the mesh
- 2. x1, x-coordinate of the lower left corner of the selected rectangle
- 3. y1, y-coordinate of the lower left corner of the selected rectangle
- 4. x2, x-coordinate of the upper right corner of the selected rectangle
- 5. y2, y-coordinate of the upper right corner of the selected rectangle
- 6. Nx, Number of points in the regular mesh along the x-direction
- 7. Ny, Number of points in the regular mesh along the y-direction
- 8. Va., Applied voltage (if the specified voltage is not available the closest value will be taken
- 9. file-name, file-name to save the data in.

surfVjplot

Export the junction voltages for a specific solution. Just like in the surfVplot command the data is interpolated and mapped on a regular mesh. The junction voltage is defined for the one and two diode models. For other models the junction voltage may not be available, in which case it is set to 0. The command takes eight arguments:

- 1. mesh-name, Name of the mesh
- 2. x1, x-coordinate of the lower left corner of the selected rectangle
- 3. y1, y-coordinate of the lower left corner of the selected rectangle
- 4. x2, x-coordinate of the upper right corner of the selected rectangle
- 5. y2, y-coordinate of the upper right corner of the selected rectangle
- 6. Nx, Number of points in the regular mesh along the x-direction
- 7. Ny, Number of points in the regular mesh along the y-direction
- 8. Va, Applied voltage (if the specified voltage is not available the closest value will be taken
- 9. file-name, file-name to save the data in.

surfPplot

Export the local power density for a specific solution. Just like in the surfVplot command the data is interpolated and mapped on a regular mesh. The command takes eight arguments:

- 1. mesh-name, Name of the mesh
- 2. x1, x-coordinate of the lower left corner of the selected rectangle
- 3. y1, y-coordinate of the lower left corner of the selected rectangle
- 4. x2, x-coordinate of the upper right corner of the selected rectangle
- 5. y2, y-coordinate of the upper right corner of the selected rectangle
- 6. Nx, Number of points in the regular mesh along the x-direction
- 7. Ny, Number of points in the regular mesh along the y-direction $\frac{1}{2}$
- 8. Va, Applied voltage (if the specified voltage is not available the closest value will be taken
- 9. file-name, file-name to save the data in.

surfJplot

Export the current densities in the electrodes and through the solar cells. Unlike the print-commands like printV the data is mapped on a regular mesh. The command takes eight arguments:

- 1. mesh-name, Name of the mesh
- 2. $\mathtt{x1},$ x-coordinate of the lower left corner of the selected rectangle
- 3. y1, y-coordinate of the lower left corner of the selected rectangle
- 4. $\mathtt{x2},$ x-coordinate of the upper right corner of the selected rectangle
- 5. y2, y-coordinate of the upper right corner of the selected rectangle
- 6. Nx, Number of points in the regular mesh along the x-direction
- 7. Ny, Number of points in the regular mesh along the y-direction
- 8. Va, Applied voltage (if the specified voltage is not available the closest value will be taken
- 9. file-name, file-name to save the data in.

surfEplot

Export the local electric field in x- and y- direction in the electrodes. Just like in the surfVplot command the data is mapped on a regular mesh. The command takes eight arguments:

- 1. mesh-name, Name of the mesh
- 2. x1, x-coordinate of the lower left corner of the selected rectangle
- 3. y1, y-coordinate of the lower left corner of the selected rectangle
- 4. x2, x-coordinate of the upper right corner of the selected rectangle
- 5. y2, y-coordinate of the upper right corner of the selected rectangle
- 6. Nx, Number of points in the regular mesh along the x-direction
- 7. Ny, Number of points in the regular mesh along the y-direction
- 8. Va., Applied voltage (if the specified voltage is not available the closest value will be taken
- 9. file-name, file-name to save the data in.

surfFc

Export the locally collected photo-current. The locally collected current is the portion of the local photo-current which is collected at the terminals. Just like in the surfVplot command the data is mapped on a regular mesh. The command sets the short circuit current density to 0 for specific points and computes the difference in terminal current. Note that the full non-linear response of the system is considered (you ask why?, why not!). The command takes 11 arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, file-name to save the data in.
- 3. connection-index, Index of the connection for which the photo-current collection is computed. The first connection, between electrode 0 and 1, has index 0
- 4. Va, applied voltage
- 5. x1, x-coordinate of the lower left corner of the selected rectangle
- 6. y1, y-coordinate of the lower left corner of the selected rectangle
- 7. x2, x-coordinate of the upper right corner of the selected rectangle
- 8. y2, y-coordinate of the upper right corner of the selected rectangle
- 9. Nx, Number of points in the regular mesh along the x-direction
- 10. Ny, Number of points in the regular mesh along the y-direction
- 11. RI, Boolean, if true the internal series resistance is considers (i.e., consider bias dependent collection of the diode due to an internal series resistance)

surffc

Export the differential local photo-current collection efficiency. The differential photo-current collection efficiency is the portion of a change in photo-current that is collected at the terminals. This is a differential value, i.e. it computes the change in terminal current for an infinitesimal small change in photo-current. Just like in the surfVplot command the data is mapped on a regular mesh. The command takes 11 arguments:

- 1. mesh-name, Name of the mesh
- 2. file-name, file-name to save the data in.
- 3. connection-index, Index of the connection for which the photo-current collection is computed. The first connection, between electrode 0 and 1, has index 0
- 4. Va, applied voltage
- 5. x1, x-coordinate of the lower left corner of the selected rectangle
- 6. y1, y-coordinate of the lower left corner of the selected rectangle
- 7. x2, x-coordinate of the upper right corner of the selected rectangle
- 8. y2, y-coordinate of the upper right corner of the selected rectangle
- 9. Nx, Number of points in the regular mesh along the x-direction
- 10. Ny, Number of points in the regular mesh along the y-direction
- 11. RI, Boolean, if true the internal series resistance is considers (i.e., consider bias dependent collection of the diode due to an internal series resistance)

Manipulating local properties

Keyword

Description

assign_properties

Assign nodes to a defined area. If no nodes are selected all nodes in the mesh are assigned to the specified area. The command takes one arguments:

1. area-name, Name of the area (<mesh-name>.<area-name>)

set_Rel

Set an electrode resistance per area. If the specified area does not exist it will be newly created. The command takes three arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. electrode-index, Index of the electrode. The first electrode has index 0
- 3. value, Sheet resistance value (Ω)

set_Rvp

Set the contact resistance between the positive node and an electrode per area. If the specified area does not exist it will be newly created. Together with set_Rvn this command allows the application of an extranal voltage. The command takes three arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. electrode-index, Index of the electrode. The first electrode has index 0
- 3. value, Contact resistance (Ωcm^2)

set_Rvn

Set the contact resistance between the negative node and an electrode per area. If the specified area does not exist it will be newly created. Together with set_Rvp this command allows the application of an extranal voltage. The command takes three arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. electrode-index, Index of the electrode. The first electrode has index 0
- 3. value, Contact resistance (Ωcm^2)

set_JV

Specify a tabular data set to use as a JV characteristics per area. If the specified area does not exist it will be newly created. The command takes three arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. file-name, Name of a file containing two columns, voltage and current density (V, Acm^{-2})

set_2DJV

Specify a two-diode model for the JV characteristics per area. If the specified area does not exist it will be newly created. The command takes eight arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. J01, Saturation current density for the first diode (ideality factor one) (Acm⁻²)
- 4. J02, Saturation current density for the second diode (ideality factor two) (Acm⁻²)
- 5. Jph, Photo current density (Acm^{-2})
- 6. Rs, Series resistance (Ωcm^2)
- 7. Rsh, Shunt resistance (Ω cm²)
- 8. Eg, Band gap (eV)

set_1DJV

Specify a one-diode model for the JV characteristics per area. If the specified area does not exist it will be newly created. The command takes eight arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. J0, Saturation current density (Acm^{-2})
- 4. nid, Ideality factor
- 5. Jph, Photo current density (Acm⁻²)
- 6. Rs, Series resistance (Ωcm^2)
- 7. Rsh, Shunt resistance (Ω cm²)
- 8. Eg, Band gap (eV)

set_PTJV

Specify the photo-transistor model for the JV characteristics per area. If the specified area does not exist it will be newly created. See the command set_PTJV_extra to set extra parameters for the model. The command takes eleven arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. Jsbc, Dark saturation current density of the main BC diode (Acm⁻²)
- 4. Jsbe, Dark saturation current density of the main BE diode (Acm⁻²)
- 5. Rs, Series resistance (Ωcm^2)
- 6. Rsh, Shunt resistance (Ωcm^2)
- 7. EgBE, Band gap of the BE diodes (eV)
- 8. PhiBC, Barrier of the BC junction (eV)
- 9. Bf, Forward operation gain
- 10. Vaf, Forward operation Early voltage (V)

set_PTJV_extra

Specify extra parameters for the photo-transistor model for the JV characteristics per area. To use this command you must first set the photo-transistor model with the command set_PTJV. The command takes ten arguments:

- 1. Jse, Dark satuartion current of the leakage BE diode (Acm⁻²)
- 2. Jsc, Dark satuartion current of the leakage BC diode (Acm⁻²)
- 3. Nf, Main BE diode ideality factor
- 4. Nr., Main BC diode ideality factor
- 5. Ne, Leakage BE diode ideality factor
- 6. Nc, Leakage BC diode ideality factor
- 7. Var, Reverse operation Early voltage (V)
- 8. XTIBE, Temperature dependency of the BE diodes
- 9. XTIBC, Temperature dependency of the BC diodes
- 10. XTIB, Temperature dependency of the forward gain

set_R

Specify a resistance for the JV characteristics per area. If the specified area does not exist it will be newly created. The command takes three arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. R, Resistance (Ωcm^2)

 $set_{-}T$

Specify a local temperature. The command takes two arguments:

- 1. area-name, Name of the area (<mesh-name>.<area-name>)
- 2. T, Temperature (K)

set_sel_Rel

Set an electrode resistance per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. The command takes three arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. electrode-index, Index of the electrode. The first electrode has index 0
- 3. value, Sheet resistance value (Ω)

set_sel_Rvp

Set the contact resistance between the positive node and an electrode per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. Together with set_Rvn this command allows the application of an extranal voltage. The command takes three arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. electrode-index, Index of the electrode. The first electrode has index 0
- 3. value, Contact resistance (Ωcm^2)

set_sel_Rvn

Set the contact resistance between the negative node and an electrode per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. Together with set_Rvp this command allows the application of an extranal voltage. The command takes three arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. electrode-index, Index of the electrode. The first electrode has index $\boldsymbol{0}$
- 3. value, Contact resistance (Ωcm^2)

 set_sel_JV

Specify a tabular data set to use as a JV characteristics per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. The command takes three arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- file-name, Name of a file containing two columns, voltage and current density (V, Acm⁻²)

set_sel_2DJV

Specify a two-diode model for the JV characteristics per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. The command takes eight arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. J01, Saturation current density for the first diode (ideality factor one) (Acm⁻²)
- 4. J02, Saturation current density for the second diode (ideality factor two) (Acm⁻²)
- 5. Jph, Photo current density (Acm⁻²)
- 6. Rs, Series resistance (Ωcm^2)
- 7. Rsh, Shunt resistance (Ω cm²)
- 8. Eg, Band gap (eV)

set_sel_1DJV

Specify a one-diode model for the JV characteristics per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. The command takes eight arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. J0, Saturation current density (Acm^{-2})
- 4. nid, Ideality factor
- 5. Jph, Photo current density (Acm⁻²)
- 6. Rs, Series resistance (Ωcm^2)
- 7. Rsh, Shunt resistance (Ω cm²)
- 8. Eg, Band gap (eV)

set_sel_PTJV

Specify the photo-transistor model for the JV characteristics per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. See the command set_sel_PTJV_extra to set extra parameters for the model. The command takes eleven arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. Jsbc, Dark saturation current density of the main BC diode (Acm⁻²)
- 4. Jsbe, Dark saturation current density of the main BE diode (Acm⁻²)
- 5. Rs, Series resistance (Ωcm^2)
- 6. Rsh, Shunt resistance (Ωcm^2)
- 7. EgBE, Band gap of the BE diodes (eV)
- 8. PhiBC, Barrier of the BC junction (eV)
- 9. Bf, Forward operation gain
- 10. Vaf, Forward operation Early voltage (V)

set_sel_PTJV_extra

Specify extra parameters for the photo-transistor model for the JV characteristics per selection. To use this command you must first set the photo-transistor model with the command set_sel_PTJV. The command takes ten arguments:

- 1. Jse, Dark satuartion current of the leakage BE diode (Acm⁻²)
- 2. Jsc, Dark satuartion current of the leakage BC diode (Acm⁻²)
- 3. Nf, Main BE diode ideality factor
- 4. Nr, Main BC diode ideality factor
- 5. Ne, Leakage BE diode ideality factor
- 6. Nc, Leakage BC diode ideality factor
- 7. Var, Reverse operation Early voltage (V)
- 8. XTIBE, Temperature dependency of the BE diodes
- 9. XTIBC, Temperature dependency of the BC diodes
- 10. XTIB, Temperature dependency of the forward gain

set_sel_R

Specify a resistance for the JV characteristics per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. The command takes three arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. connection-index, Index of the connection. The first connection, between electrode 0 and 1, has index 0
- 3. R, Resistance (Ωcm^2)

 set_sel_T

Specify a local temperature per selection, i.e. change a parameter for all elements within a selection. If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. The command takes two arguments:

- 1. area-name, Area name modifier (<mesh-name>.<modifier>)
- 2. T, Temperature (K)

Numerical Settings

Keyword set_SplitX

Description

It is sometimes useful to prevent the adaptive meshing algorithms from splitting certain nodes in x-or y-direction. This commands toggles the splitting of nodes in x-direction for a specified area (per default all nodes can be split in all directions). The command takes one argument:

1. area-name, Name of the area (<mesh-name>.<area-name>)

set_SplitY

It is sometimes useful to prevent the adaptive meshing algorithms from splitting certain nodes in xor y-direction. This commands toggles the splitting of nodes in y-direction for a specified area (per default all nodes can be split in all directions). The command takes one argument:

1. ${\tt area-name},$ Name of the area (<mesh-name>.<area-name>)

set_sel_SplitX

It is sometimes useful to prevent the adaptive meshing algorithms from splitting certain nodes in x-or y-direction. This commands toggles the splitting of nodes in x-direction for a selection (per default all nodes can be split in all directions). If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. The command takes one argument:

1. area-name, Area name modifier (<mesh-name>.<modifier>)

set_sel_SplitY

It is sometimes useful to prevent the adaptive meshing algorithms from splitting certain nodes in x-or y-direction. This commands toggles the splitting of nodes in y-direction for a selection (per default all nodes can be split in all directions). If no elements are selected this command sets a parameter for all areas. If elements are selected this command may create new areas to make sure the change is confined to the selected elements. To do this it appends an area modifier name to existing area names. If the modified area name already exists the modifications are applied to this existing area. The command takes one argument:

1. area-name, Area name modifier (<mesh-name>.<modifier>)

maxiter

Set the maximum number of iterations for solving the non-linear system. The command takes one argument:

1. maxiter, Maximum number of iterations (default: 25)

tol_V

Absolute voltage tolerance for the break-off criterion. The command takes one argument:

1. tol_V, Absolute voltage tolerance V (default: 10^{-5} V)

rel tol V

Relative voltage tolerance for the break-off criterion. The command takes one argument:

1. tol_V, Relative voltage tolerance – (default: 10^{-5})

tol_kcl

Absolute current tolerance for the break-off criterion (KCL stands for Kirchhoff's Current Law). The command takes one argument:

1. tol_kcl, KCL tolerance A (default: 10^{-5} A)

rel_tol_kcl

Relative current tolerance for the break-off criterion (KCL stands for Kirchhoff's Current Law). The command takes one argument:

1. tol_kcl, Relative KCL tolerance – (default: 10^{-5})

N_Lin_Search

Number of steps for a linear search in the Newton-Raphson direction. If an iterative adaption of the potentials would lead to increase of the error in the Kirchhoff Current Laws, we perform a linear search in the Newton-Raphson direction. If a better solution is not found within the number of steps specified, Gmin stepping is initiated (see the settings GminSteps, GminMax, and GminFac. The command takes one argument:

1. N, Number of steps – (default: 10)

GminStep

Number of Gmin stepping steps. In case of convergence problems Gmin stepping is triggered. In Gmin stepping a minimum conductance is placed in parallel with all non-linear devices. The value of the minimum conductance is then step wise reduced to 0. This parameter is used in conjunction with GminMax and GminFac. The command takes one argument:

1. N, Number of steps - (default: 6)

GminMax

Maximum value of the minimum conductance. In case of convergence problems Gmin stepping is triggered. In Gmin stepping a minimum conductance is placed in parallel with all non-linear devices. The value of the minimum conductance is then step wise reduced to 0. This value sets the initial minimum conductance after Gmin stepping is triggered. This parameter is used in conjunction with GminSteps and GminFac. The command takes one argument:

1. Gmin, Minimum conductance Ω^{-1} cm⁻² (default: 10^{-2})

GminFac

Factor to step-wise reduce Gmin during Gmin stepping. In case of convergence problems Gmin stepping is triggered. In Gmin stepping a minimum conductance is placed in parallel with all non-linear devices. The value of the minimum conductance is then step wise reduced to 0. This value controls the rate with which the Gmin value is reduced (higher is faster). This parameter is used in conjunction with GminSteps and GminMax. The command takes one argument:

1. f, Factor to reduce Gmin – (default: 10)

GminStart

In poorly converging cases it may be beneficial to start with one or more iterations with a minimum conductance. This parameter allows you to specify a number of iterations run with a Gmin value set by GminMax. Note that this procedure is different from Gmin stepping as the Gmin value is not changed during these iterations and abruptly changes from the GminMax value to Gmin after the set number of iterations. A typical setting would be 1.

1. GminStart, Number of GminStart iterations - (default: 0)

Gmin

Set the overall Gmin value. This value is always used and should therefore be small as otherwise it affects the results.

1. Gmin, Minimum conductance Ω^{-1} cm⁻² (default: 0.0)

Solving

Keyword solve

Description

Solve the system (do a voltage sweep). The command takes four arguments:

- 1. mesh-name, Name of the mesh
- 2. V_start, Start voltage
- 3. V_end, End voltage
- 4. N_step, Number of voltage steps

refine_oc

Given a voltage sweep is present which includes voltages above and below V_{oc} , this command tries to refine the IV characteristics to include the open circuit point. The command takes four arguments:

- 1. mesh-name, Name of the mesh
- 2. tol_i, current tolerance
- 3. tol_v, voltage tolerance
- 4. Nmax, Maximum number of iterations

refine_mpp

Given a voltage sweep is present of at least three points, which includes voltages above and below V_{mpp} , this command tries to refine the IV characteristics to include the maximum power point. The command takes four arguments:

- 1. mesh-name, Name of the mesh
- 2. tol_i, current tolerance
- 3. tol_v, voltage tolerance
- 4. Nmax, Maximum number of iterations

adaptive_solve

Solve the system and adapt the mesh at one specified voltage. The command takes four arguments:

- 1. mesh-name, Name of the mesh
- 2. V_a, Applied voltage
- 3. threshold, Relative threshold for node splitting, a parameter between 0 and 1 that controls how aggressive the mesh is adapted, where lower values lead to a more aggressive mesh adaption (typical values between 0.3 and 0.5).
- 4. N_step, Number adaptive meshing iterations

Verbosity Levels

Keyword	Description					
out_quiet	Set verbosity to the minimum (only says something when it crashes). The command takes no arguments.					
out_normal	Set verbosity to the normal level. The command takes no arguments.					
out_verbose Output additional data that may be interesting. The command takes no arguments.						
out_debug	Output additional data that is only interesting for someone who is chasing bugs in the code. The command takes no arguments.					
Misc.						
Keyword	Description					
tic	Start the timer.					
toc	Print seconds since last tic command (or start of execution if no tic command was issued)					

define

Define a variable. PVMOS variables only support numerical values. These variables can be used wherever a numerical value is required (see Section VIB). The command takes two arguments:

- 1. name, name of the variable
- 2. value, value of the variable

define_solpar

Determine the solar cell parameters from the simulated IV points for a mesh and define the variables Isc, Voc, Impp, and Vmpp, with their values set accordingly. These variables can be used wherever a numerical value is required (see Section VIB). The command takes one argument:

1. mesh-name, name of the mesh

define bb

Determine the bounding box of a mesh and store the results in the variables x1, y1, x2, and y2, where (x1, y1) is the coordinate for the lower left corner and (x1, y1) the upper right corner. These variables can be used wherever a numerical value is required (see Section VIB). The command takes one argument:

1. mesh-name, name of the mesh

B. Variables and expressions

PVMOS also features "expressions", which are placed between square brackets, i.e., [<expression>]. You can refer to variables, as defined with the define command (see the previous section), in expressions. Furthermore, PVMOS can evaluate mathematical expressions, provided PVMOS is compiled with libmatheval support. Expressions can be placed anywhere in the PVMOS input file, also as part of a word. Nesting of expressions is also allowed. Perhaps the best way to explain the use of expressions is with a few examples.

Define N = 10:

define N 10

Initialize mesh10:

newmesh 0 0 1 1 [N] [N] mesh[N]

Define some variables and calculate with them:

define Jph 0.03

define kT 0.0259

define J0 1e-12

define Voc [kT*log(Jph/J0+1)]

PVMOS with libratheval supports the following functions:

- \bullet exp exponential
- log logarithmic
- sqrt square root
- sin sine
- cos cosine
- tan tangent
- cot cotangent
- sec secant
- csc cosecant
- asin inverse sine
- acos inverse cosine
- atan inverse tangent
- acot inverse cotangent

- asec inverse secant
- acsc inverse cosecant
- sinh hyperbolic sine
- cosh cosine
- tanh hyperbolic tangent
- coth hyperbolic cotangent
- \bullet sech hyperbolic secant
- csch hyperbolic cosecant
- asinh hyperbolic inverse sine
- acosh hyperbolic inverse cosine
- \bullet atanh hyperbolic inverse tangent
- acoth hyperbolic inverse cotangent
- asech hyperbolic inverse secant
- acsch hyperbolic inverse cosecant
- abs absolute value
- step with value 1 defined for x = 0 Heaviside step function
- nandelta Dirac delta function with not-a-number at x=0
- delta Dirac delta function with infinity at x = 0
- erf error function

In addition libratheval defines the following constants:

- e e
- log2e $\log 2(e)$
- \bullet log10e $\log 10(e)$
- ln2 ln(2)
- ln10 ln(10)
- \bullet pi π
- \bullet pi_2 $\pi/2$
- \bullet pi_4 $\pi/4$
- \bullet 1_pi $1/\pi$
- \bullet 2_pi $2/\pi$
- 2_sqrtpi $2/\sqrt(\pi)$
- sqrt $\sqrt(2)$
- $sqrt1_2 \sqrt{(1/2)}$

Note that function and constant names cannot be redefined as a variable.

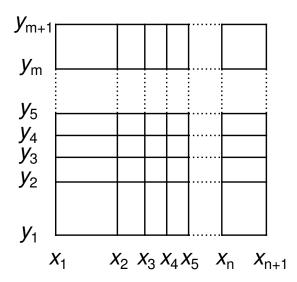


FIG. 1: The mesh topology of meshes created by mkpvmosmesh.

VII. THE PVMOS-MESH PACKAGE FOR GNU OCTAVE

The GNU Octave package PVMOS-mesh allows you to crate and save meshies in binary format for use in PVMOS. GNU Octave is a versatile Matlab-like program. Linking to Octave allows you to, for example, use GNU Octave's ability to work with bitmap images when creating a mesh for a given problem. In general GNU Octave is very good for creating and manipulating matrices. The PVMOS library allows you to create meshes in PVMOS for which the mesh topology can be represented as a matrix, i.e. the elements must be organized in rows and columns. This disallows sub-grids, however, it does allow you to vary the width and height of the rows and columns, i.e. a rudimentary variable mesh can be created.

The core of the library is the "mkpvmosmesh" function, which creates and saves a mesh for PVMOS. There are several utility functions to ease the creation of the data structures used by mkpvmosmesh from, for example, images. We start by describing the input required by the mkpvmosmesh command.

mkpvmosmesh(Na, Nel, Area_Index, Area_Def, x, y, filename)

- Na, The number or area's in the mesh
- Nel, The number or electrodes
- Area_Index, A matrix with index numbers, each number referring to one area
- Area_Def, The area definition struct array describing the properties of each area
- x, A vector with x coordinates of element boundaries
- y, A vector with y coordinates of element boundaries
- filename, A string containing the filename for the resulting PVMOS mesh

In Fig. 1 shows the topology of meshes created by mkpvmosmesh. The depicted mesh would be $m \times n$ -elements. To specify the widths and heights of the columns and rows, respectively, n+1 x- and m+1 y-coordinates are specified (i.e., the x and y vectors for the mkpvmosmesh command). For this mesh the Area_Index would be an $m \times n$ matrix with integers assigning each element to one area. The Area_Def struct-array described the properties of each area. Note that a struct is a data structure containing various fields. In this case the various field describe various properties of an area, e.g. electrode sheet resistances and diode properties. The numbers in the Area_Index matrix should correspond to index numbers of the Area_Def struct-array.

The fields in the area definition struct are presented in Table II. Within the area definition struct there is a struct array of the connection struct, describing the inter electrode connections. The connection struct fields are listed and described in IV

TABLE II: The fields in the area definition struct

Field	Default Value	Unit	Description
name	"default" -	-	String with the area name. Take care that the
			names should be unique!
Rel	1	$[\Omega]$	Array of length Nel with the sheet resistance of
			each electrode.
Rvp	-1	$[\Omega \text{cm}^2]$	Array of length Nel with the resistance to the pos-
			itive node (external voltage source). If the value is
			negative the elements will have no direct connec-
		0	tion to the external source.
Rvn	-1	$[\Omega \text{cm}^2]$	
			ground node (external voltage source). If the value
			is negative the elements will have no direct connec-
		r3	tion to the external source.
T	300		Scalar value for the temperature in the area
SplitX	1 -	-	Boolean value (0 is false, 1 is true) indicating
			whether an element can be split in the x-direction
			during adaptive meshing. If set to 0 the element
a	_		will not be split.
SplitY	1 -	-	Boolean value (0 is false, 1 is true) indicating
			whether an element can be split in the y -direction
			during adaptive meshing. If set to 0 the element
			will not be split.
conn		-	Structure array of length Nel-1 with the properties
			of the connection between the electrodes

TABLE IV: The fields in the connection struct

Field	Default Value Un	nit	Description
model	"ONED" -		String with the model name. Possible models are:
			ONED One diode model
			TWOD Two diode model
			PHOTOT Photo-transistor model
T 1	0. [4	-21	JVD Tabular JV data
Jph			Photo-current density for the models ONED, TWOD, and PHOTOT
Rs	1e-5 [Ωc	cm^2]	Series resistance for the models ONED, TWOD, and PHOTOT
Rsh	1e3 [Ωc	cm^2]	Shunt resistance for the models ONED, TWOD, and PHOTOT $$
J01	1e-12 [Ac	cm^{-2}]	Dark saturation current for the first diode, used in models ONED and TWOD
J02	1e-8 [Ac	cm^{-2}]	Dark saturation current for the second diode, used
	1 []		in model TWOD
nid1	1 [-]		Ideality factor of the first diode, used in models ONED and TWOD
nid2	2 [-]		Ideality factor of the second diode, used in model TWOD
Eg	1.2 [eV	V]	Band gap of the diode, used in models ONED and TWOD
$_{ m Jsbc}$	5e-4 [Ad	cm^{-2}	Dark saturation current density of the main BC diode
$_{ m Jsbe}$	5e-15 [Ac	cm^{-2}	Dark saturation current density of the main BE diode
$_{ m Jse}$	0 [Ac	cm^{-2}	Dark satuartion current of the leakage BE diode
$_{ m Jsc}$			Dark satuartion current of the leakage BC diode
Nf	1 [-]	J	Main BE diode ideality factor
Nr	1 [-]		Main BC diode ideality factor
Ne	1.5 [-]		Leakage BE diode ideality factor
Nc	2 [-]		Leakage BC diode ideality factor
Vaf	∞ [V]]	Forward operation Early voltage
Var	∞ [V]]	Reverse operation Early voltage
Bf_{-}	3 [-]		Forward operation gain
EgBE	1.2 [eV		Band gap of the BE diodes
PhiBC	0.3 [eV]	/]	Barrier of the BC junction
XTIBE	L J		Temperature dependency of the BE diodes
XTIBC XTIB			Temperature dependency of the BC diodes
VIID	3 [-]		Temperature dependency of the forward gain

Several commands are provided to ease the use of the mkpvmosmesh command. To initialize the area definition struct array (Area_Def), the package provides the function:

Area_Def=PVMOS_AreaProperties(Nel)

It initializes the struct array with one area, using the default values listed in Tables II and IV.

I feel it is convenient to work with "selection masks" when defining new areas. A selection mask is essentially a matrix, with the same size as the Area_Index matrix, i.e. one matrix element per mesh element, where a 1 selects the element and a 0 not. There are two functions that allow you to use masks to build up the various areas in the Area_Index matrix and the Area_Def area definition struct array. The functions are:

[Area_Index, Area_Def] = PVMOS_SetMask(Area_Index, Area_Def, mask, Mask_Area)

- Area_Index, A matrix with index numbers, each number referring to one area
- Area_Def, The area definition struct array describing the properties of each area
- mask, Mesh element selection mask
- Mask_Area, Area definition struct to apply to the selected elements (i.e. this area definition will be added to the Area_Def area definition struct array)

and

[Area_Index, Area_Def] = PVMOS_ModifyMask(Area_Index,Area_Def, mask, modlist, name)

- Area_Index, A matrix with index numbers, each number referring to one area
- Area_Def, The area definition struct array describing the properties of each area
- mask, Mesh element selection mask
- modlist, Cell array specifying the properties to be changed for the given elements
- name, String with the addition to the area names for the selected elements

The difference between the functions is that PVMOS_SetMask sets the area for the selected elements and adds one area to the mesh, whereas the PVMOS_ModifyMask changes only selected properties for the selected elements, creating as many areas as required. The newly created areas keep the name of the area's they were created from but with the addition of the name string at the end of the area name.

VIII. EXAMPLES

In this section I discuss several examples which can be found in the example directory.

A. Monolithically series connected mini-module and a defect

In the folder Examples/ThinFilm you can find a PVMOS input file thin_film8x8.mos. This file creates a thin-film a-Si:H mini-module of 8x8 cm² with 8 cells of 1 cm wide. In addition the third cell has a defect. This example demonstrates many basic PVMOS operations such as creating new meshes, joining meshes, selecting elements, locally refine the mesh, create new area's, setting parameters for area's, and assigning elements to an area.

B. Monolithically series connected mini-module and many defects

This example consists of the files thin_film40x40.mos and Shunts40x40.m, both located in Examples/ThinFilm. This example depends on GNU Octave. In this example I use the file thin_film40x40.mos to create a 40x40 cm² module with 40 cells of 1 cm wide. The module that is created is defect-free. In the file thin_film40x40.mos no simulation is run, the script only creates a defect free mesh which is saved to a binary file. The GNU Octave script Shunts40x40.m creates a random distribution of defects and generates PVMOS scripts where these defects are built in. The PVMOS scripts generated by the GNU Octave script start by loading the defect-free mesh and subsequently locally refine the mesh and add shunts. This script demonstrates the simulation of larger systems (and for that reason is best used on a 64 bit operating system and a 64bit PVMOS executable and several GB of memory) and the saving and loading of meshes.

C. Metal wrap-through module

This example is located in Examples/Pinup. The example entails the files several files:

- mkpvmosmesh.oct Dynamic library for GNU Octave to write PVMOS meshes. This needs to be compiled from the PVMOS source tree ("make mkpvmosmesh") and placed in the example directory.
- generate_mesh.m Generates the mesh from the images listed below using GNU octave
- pinup_frontmetal.png Image used by generate_mesh.m to define the areas where there is metal at the front
- pinup_vias.png Image used by generate_mesh.m to define the areas where the front contact is connected to the contact foil through vias
- pinup_backisolation.png Image used by generate_mesh.m to define the areas where the back contact is isolating (around the vias)
- pinup_back2contactfoil.png Image used by generate_mesh.m to define the areas where the back contact is connected to the contact foil
- pinup_foilisolation.png Image used by generate_mesh.m to define the areas where the contact foil is isolating
- pinup_contactfoil_vn.png Image used by generate_mesh.m to define the areas the contact foil is connected to ground
- pinup_contactfoil_vp.png Image used by generate_mesh.m to define the areas where the contact foil is connected to the positive node.
- pinup.mos The PVMOS input file

This example demonstrates how a PVMOS mesh can be generated from images using GNU octave where the images are used as selection masks to select elements and change some parameters for these elements. The example simulateds a metal wrap-through solar cell with three electrose, the front electrode (emitter and front metal), the back electrode (metal contact to the base) and a contact foil at the back which contacts the front metal through vias and the back contact. After running the <code>generate_mesh.m</code> script in GNU Octave a mesh is written to <code>pinup.bin</code>. This meash is loaded in the PVMOS script <code>pinup.mos</code>. As the mesh is rather large the mesh is first simplified to reduce the number of elements in the mesh without losing resolution in he area definition. After this step the mesh is a tad coarse for simulating the potentials accurately so the mesh is refined again but this time only there where mesh refinement is needed for an accurate simulation of the potentials. After that the device IV characteristics are simulated.

D. Crystalline silicon module

The final example is perhaps the most elaborate. In Examples/CSiSTD we do a simulation of a crystalline solar cell with three bus-bars. The simulation extensively uses the definition of new meshes which are glued together to form bigger and more complicated meshes until we have a complete cell with bus-bars and fingers and tabbing wires. It uses all the tricks PVMOS has to generate a complicated geometry from scratch without aid from GNU Octave. The result is a mesh that is comparatively small and therefore allows to do the simulation is a comparatively small

memory footprint (less than 0.5 GB) which makes this example even suitable for 32bit machines. There is an optional section in the input file which you can un-comment to simulate the effect of Banksy spray-painting a rat on your solar cell leaving a permanent rat-shaped shadow pattern on the cell.

^[1] B. E. Pieters, "PVMOS: A Free and Open Source Simulation Tool for Solar Modules," submitted to: Solar Energy Materials and Solar Cells, 2015.

^[2] T. A. Davis. (retrieved 22 May 2014) BLAS performance bug and its effect on sparse "bench" in MATLAB 7.4. [Online]. Available: http://www.cise.ufl.edu/research/sparse/cholmod/blasbug.html